

Abstract of the Disclosure

A passivation layer comprises a titanium-doped aluminum oxide layer for passivation of ferroelectric materials such as Pt/SBt/Ir-Ta-O devices. The titanium-doped aluminum oxide layer for passivation of ferroelectric materials has reduced stress and improved passivation properties, and is easy to deposit and be oxidized. The passivation layer in the MFM Structure resists breakdown and peeling during annealing of the device in a forming gas ambient.